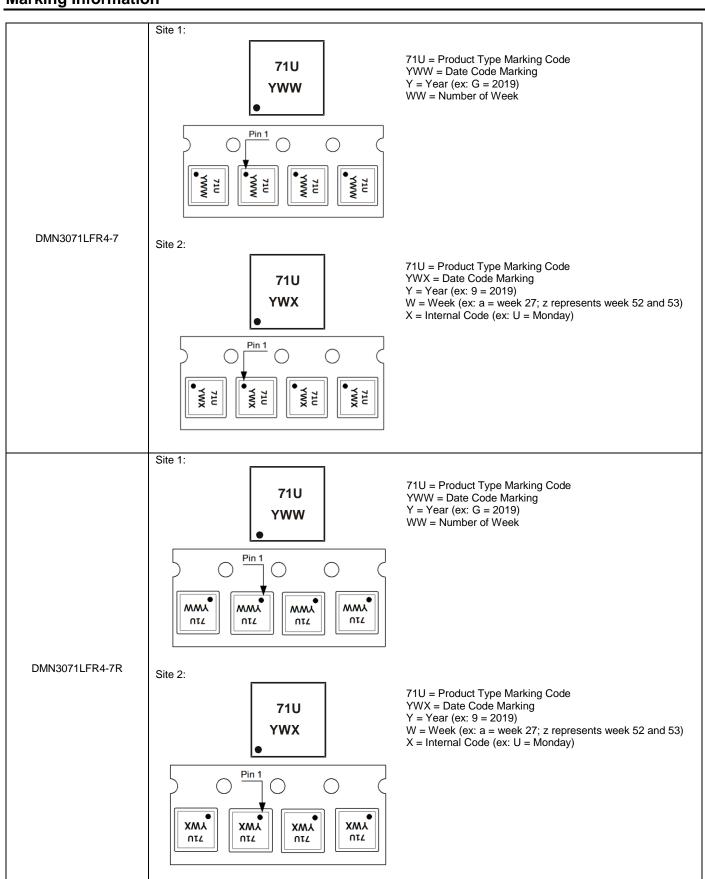


Marking Information





Marking Information (Cont.)

Site 1:

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	Н	I	J	K	L	M

Site 2:

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	8	9	0	1	2	3	4	5

Ī	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	3.4 2.7	А
Maximum Continuous Body Diode Forward Current (I _S	1.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	15	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	221	°C/W
Total Power Dissipation (Note 6)		P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	107	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance				65	mΩ	$V_{GS} = 10V, I_D = 3.2A$
Static Diani-Source On-Resistance	R _{DS(ON)}	_	_	75	11122	$V_{GS} = 4.5V, I_D = 3.2A$
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}		190	_		151/11/ 01/
Output Capacitance	Coss	I	36	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	26	_		1 = 1:0\vii 12
Gate Resistance	Rg	_	4.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	2.1	_		
Total Gate Charge (V _{GS} = 10V)	Qg	_	4.5	_	nC	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Gate-Source Charge	Qgs	_	0.5	_	IIC IIC	$V_{DS} = 15V, I_D = 4A$
Gate-Drain Charge	Q_{qd}	_	0.8	_		
Turn-On Delay Time	t _{D(ON)}	_	1.7	_		
Turn-On Rise Time	t _R	_	5.7	_		V _{DS} = 15V, V _{GS} = 10V.
Turn-Off Delay Time	t _{D(OFF)}	_	6.0	_	ns	$R_G = 3\Omega$, $I_D = 4A$
Turn-Off Fall Time	t _F	-	1.6	_	1	, <u>-</u>
Reverse Recovery Time	t _{RR}	_	4.2	_	ns	1 40 11/11 4000/
Reverse Recovery Charge	Q _{RR}	_	0.5	_	nC	I _F = 4A, di/dt = 100A/μs

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.





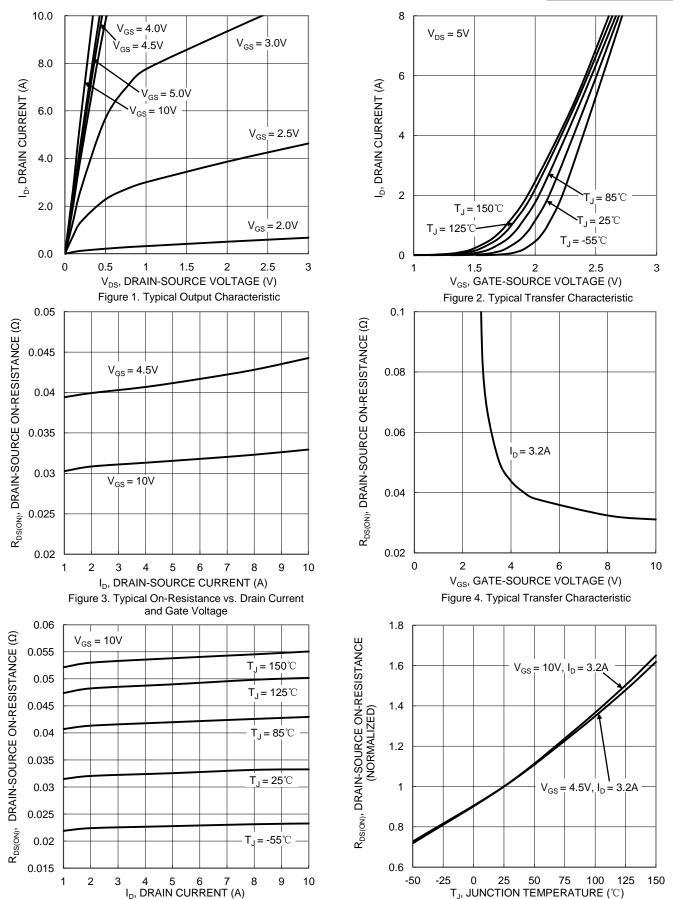


Figure 5. Typical On-Resistance vs. Drain Current

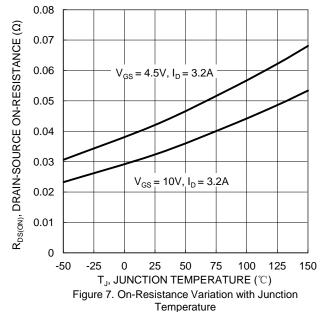
and Junction Temperature

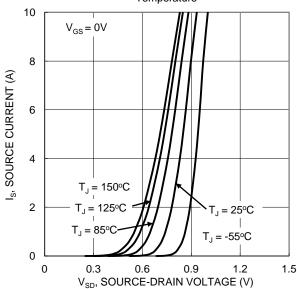
Figure 6. On-Resistance Variation with Junction

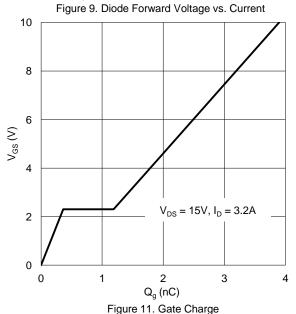
Temperature





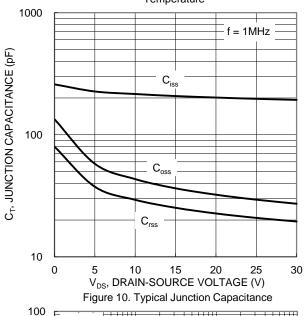


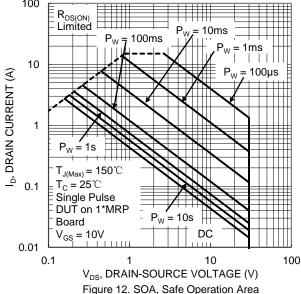




1.8 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 1.6 $I_D = 1 \text{mA}$ 1.4 1.2 $I_{D} = 250 \mu A$ 1 0.8 0.6 50 75 100 125 -50 -25 0 25 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 8. Gate Threshold Variation vs. Junction

Figure 8. Gate Threshold Variation vs. Junction Temperature







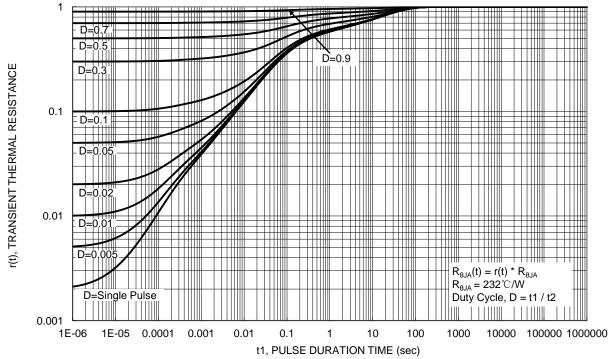


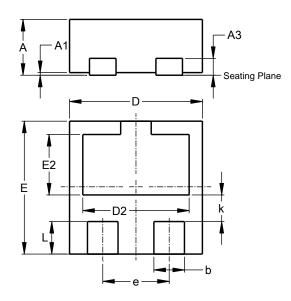
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-3

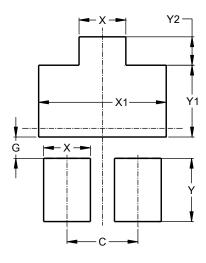


	X2-DF	N1010-3	3				
Dim	Min	Max	Тур				
Α	-	0.40	0.39				
A 1	0.00	0.05	0.02				
А3	-	-	0.13				
b	0.18	0.28	0.23				
D	0.95	1.05	1.00				
D2	0.70	0.90	0.80				
Е	0.95	1.05	1.00				
E2	0.36	0.56	0.46				
е	-	-	0.50				
k	-	-	0.20				
L	0.195	0.295	0.245				
Α	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1010-3



Dimensions	Value
	(in mm)
С	0.500
G	0.150
Х	0.330
X1	0.900
Υ	0.445
Y1	0.505
Y2	0.200



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